

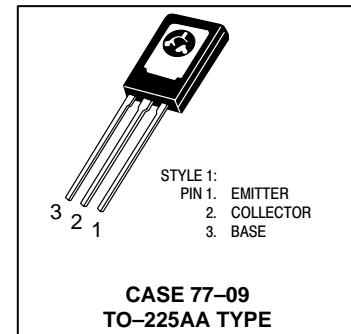
Plastic Medium-Power PNP Silicon Transistors

... designed for use in general-purpose amplifier and switching circuits. Recommended for use in 5 to 20 Watt audio amplifiers utilizing complementary symmetry circuitry.

- DC Current Gain —
 $h_{FE} = 40 \text{ (Min) @ } I_C$
 $= 1.0 \text{ Adc}$
- MJE371 is Complementary to NPN MJE521

MJE371

**4 AMPERE
POWER TRANSISTOR
PNP SILICON
40 VOLTS
40 WATTS**



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	40	Vdc
Collector–Base Voltage	V_{CB}	40	Vdc
Emitter–Base Voltage	V_{EB}	4.0	Vdc
Collector Current — Continuous — Peak	I_C	4.0 8.0	Adc
Base Current — Continuous	I_B	2.0	Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	40 320	Watts mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	θ_{JC}	3.12	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Sustaining Voltage (1) ($I_C = 100 \text{ mAdc}, I_B = 0$)	$V_{CEO(sus)}$	40	—	Vdc
Collector–Base Cutoff Current ($V_{CB} = 40 \text{ Vdc}, I_E = 0$)	I_{CBO}	—	100	μAdc
Emitter–Base Cutoff Current ($V_{EB} = 4.0 \text{ Vdc}, I_C = 0$)	I_{EBO}	—	100	μAdc

ON CHARACTERISTICS

DC Current Gain (1) ($I_C = 1.0 \text{ Adc}, V_{CE} = 1.0 \text{ Vdc}$)	h_{FE}	40	—	—
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(1) Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

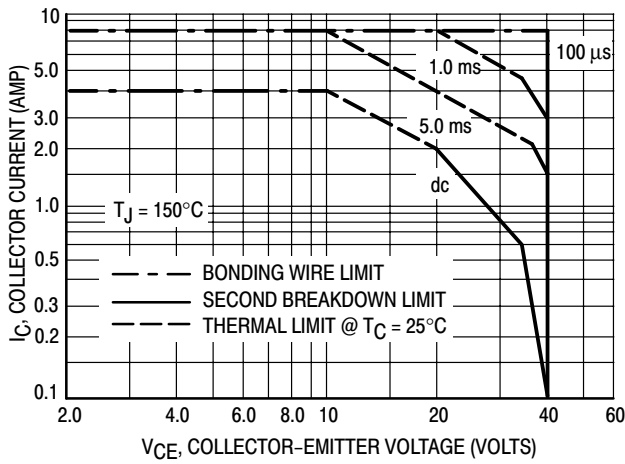


Figure 1. Active-Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 1 is based on $T_{J(pk)} = 150^\circ\text{C}$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^\circ\text{C}$. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

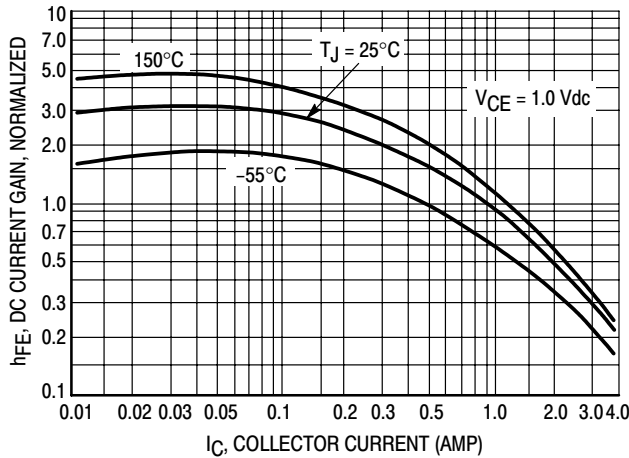


Figure 2. DC Current Gain

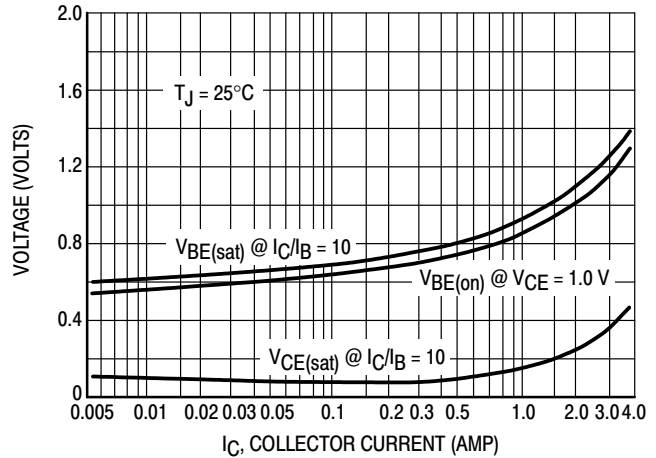


Figure 3. "On" Voltage

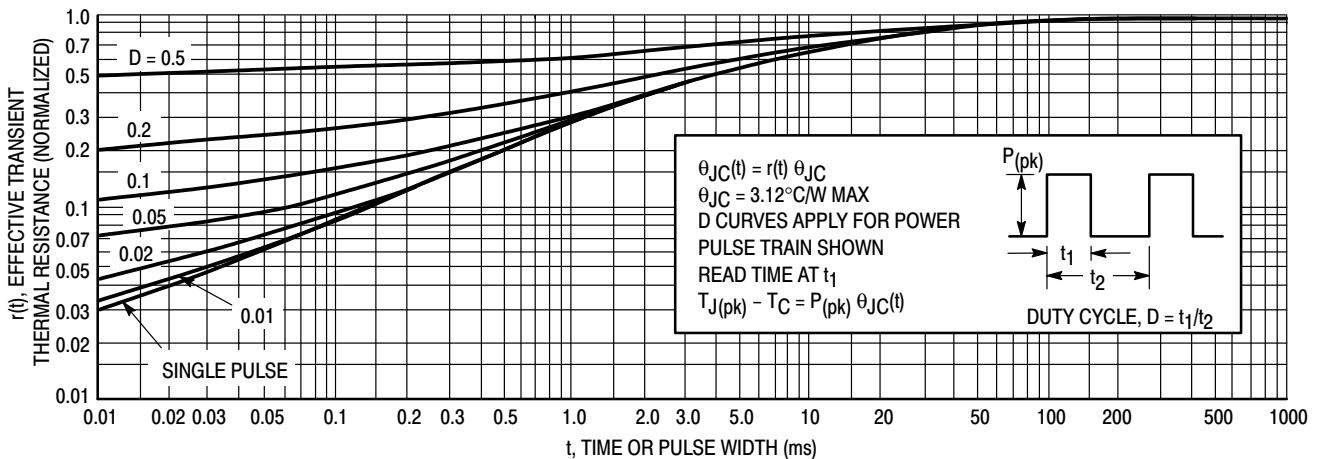
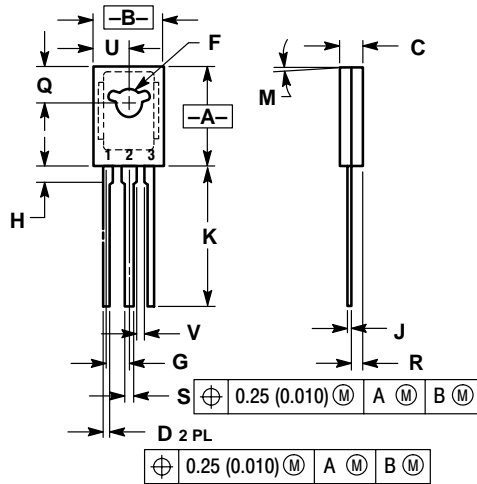


Figure 4. Thermal Response

MJE371

PACKAGE DIMENSIONS

TO-225AA
CASE 77-09
ISSUE W




NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.425	0.435	10.80	11.04
B	0.295	0.305	7.50	7.74
C	0.095	0.105	2.42	2.66
D	0.020	0.026	0.51	0.66
F	0.115	0.130	2.93	3.30
G	0.094 BSC		2.39 BSC	
H	0.050	0.095	1.27	2.41
J	0.015	0.025	0.39	0.63
K	0.575	0.655	14.61	16.63
M	5° TYP		5° TYP	
Q	0.148	0.158	3.76	4.01
R	0.045	0.065	1.15	1.65
S	0.025	0.035	0.64	0.88
U	0.145	0.155	3.69	3.93
V	0.040	---	1.02	---

STYLE 1:

1. EMITTER
2. COLLECTOR
3. BASE

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